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Stocking Distributor

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[Vishay Semiconductor/Diodes Division](#)
[16TTS08FP](#)

For any questions, you can email us directly:

sales@integrated-circuit.com



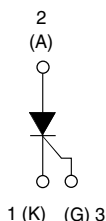
16TTS..FP High Voltage Series

Vishay High Power Products

Phase Control SCR TO-220AB FULL-PAK, 16 A



TO-220AB FULL-PAK



DESCRIPTION/FEATURES

The 16TTS..FP High Voltage Series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

Typical applications are in input rectification (soft start) and these products are designed to be used with Vishay HPP input diodes, switches and output rectifiers which are available in identical package outlines.

Fully isolated package ($V_{INS} = 2500 V_{RMS}$) is UL E78996 approved

This product has been designed and qualified for industrial level.

PRODUCT SUMMARY

V_T at 10 A	1.4 V
I_{TSM}	200 A
V_{RRM}	800/1200 V

OUTPUT CURRENT IN TYPICAL APPLICATIONS

APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS
Capacitive input filter $T_A = 55\text{ °C}$, $T_J = 125\text{ °C}$, common heatsink of 1 °C/W	13.5	17	A

MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$	Sinusoidal waveform	10	A
I_{RMS}		16	
V_{DRM}/V_{RRM}		800/1200	V
I_{TSM}		200	A
V_T	10 A, $T_J = 25\text{ °C}$	1.4	V
dV/dt		500	V/μs
dI/dt		150	A/μs
T_J	Range	- 40 to 125	°C

VOLTAGE RATINGS

PART NUMBER	V_{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V_{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I_{RRM}/I_{DRM} AT 125 °C mA
16TTS08FP	800	800	10
16TTS12FP	1200	1200	

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ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS
			TYP.	MAX.	
Maximum average on-state current	$I_{T(AV)}$	$T_C = 95\text{ }^{\circ}\text{C}$, 180° conduction, half sine wave	10		A
Maximum RMS on-state current	I_{RMS}		16		
Maximum peak, one-cycle, non-repetitive surge current	I_{TSM}	10 ms sine pulse, rated V_{RRM} applied	170		
		10 ms sine pulse, no voltage reapplied	200		
Maximum I^2t for fusing	I^2t	10 ms sine pulse, rated V_{RRM} applied	144		A ² s
		10 ms sine pulse, no voltage reapplied	200		
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	$t = 0.1$ to 10 ms, no voltage reapplied	2000		A ² √s
Maximum on-state voltage drop	V_{TM}	10 A, $T_J = 25\text{ }^{\circ}\text{C}$	1.4		V
On-state slope resistance	r_t	$T_J = 125\text{ }^{\circ}\text{C}$	24.0		mΩ
Threshold voltage	$V_{T(TO)}$		1.1		V
Maximum reverse and direct leakage current	I_{RM}/I_{DM}	$T_J = 25\text{ }^{\circ}\text{C}$	$V_R = \text{Rated } V_{RRM}/V_{DRM}$		0.5
		$T_J = 125\text{ }^{\circ}\text{C}$			10
Holding current	I_H	Anode supply = 6 V, resistive load, initial $I_T = 1$ A 16TTS08FP, 16TTS12FP	-	100	mA
Maximum latching current	I_L	Anode supply = 6 V, resistive load	200		
Maximum rate of rise of off-state voltage	dV/dt		500		V/μs
Maximum rate of rise of turned-on current	dI/dt		150		A/μs

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS
Maximum peak gate power	P_{GM}		8.0		W
Maximum average gate power	$P_{G(AV)}$		2.0		
Maximum peak positive gate current	+ I_{GM}		1.5		A
Maximum peak negative gate voltage	- V_{GM}		10		V
Maximum required DC gate current to trigger	I_{GT}	Anode supply = 6 V, resistive load, $T_J = -10\text{ }^{\circ}\text{C}$	90		mA
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^{\circ}\text{C}$	60		
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^{\circ}\text{C}$	35		
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, $T_J = -10\text{ }^{\circ}\text{C}$	3.0		V
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^{\circ}\text{C}$	2.0		
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^{\circ}\text{C}$	1.0		
Maximum DC gate voltage not to trigger	V_{GD}	$T_J = 125\text{ }^{\circ}\text{C}$, $V_{DRM} = \text{Rated value}$	0.2		mA
Maximum DC gate current not to trigger	I_{GD}		2.0		

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS
Typical turn-on time	t_{gt}	$T_J = 25\text{ }^{\circ}\text{C}$	0.9		μs
Typical reverse recovery time	t_{rr}	$T_J = 125\text{ }^{\circ}\text{C}$	4		
Typical turn-off time	t_q		110		



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THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		- 40 to 125	°C
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	1.5	°C/W
Maximum thermal resistance, junction to ambient	R _{thJA}		62	
Typical thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth and greased	1.5	
Approximate weight			2	g
			0.07	oz.
Mounting torque	minimum		6 (5)	kgf · cm
	maximum		12 (10)	(lbf · in)
Marking device		Case style TO-220AB FULL-PAK (94/V0)	16TTS08FP	
			16TTS12FP	

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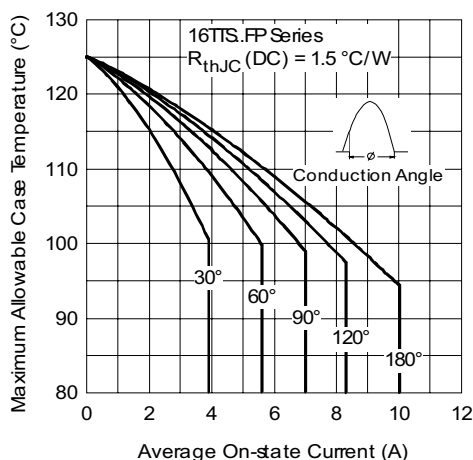


Fig. 1 - Current Rating Characteristics

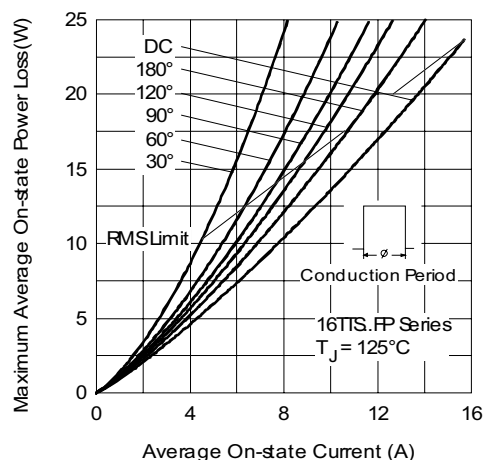


Fig. 4 - On-State Power Loss Characteristics

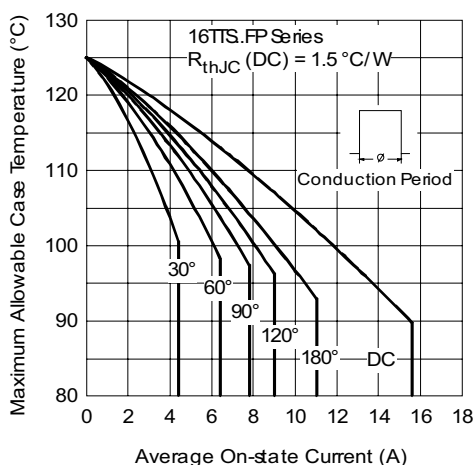


Fig. 2 - Current Rating Characteristics

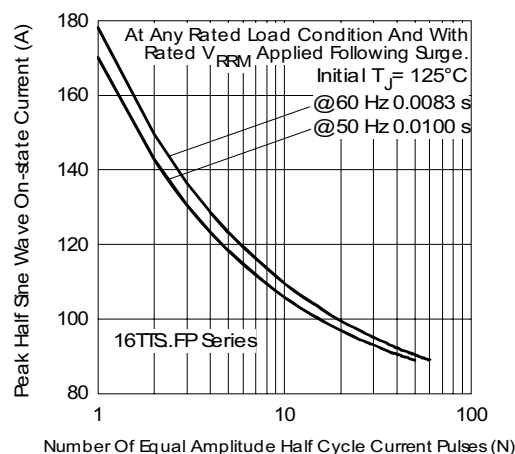


Fig. 5 - Maximum Non-Repetitive Surge Current

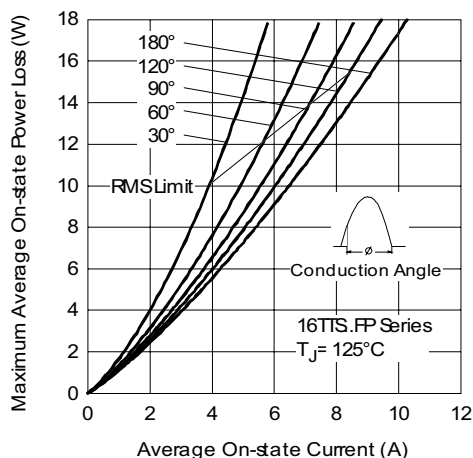


Fig. 3 - On-State Power Loss Characteristics

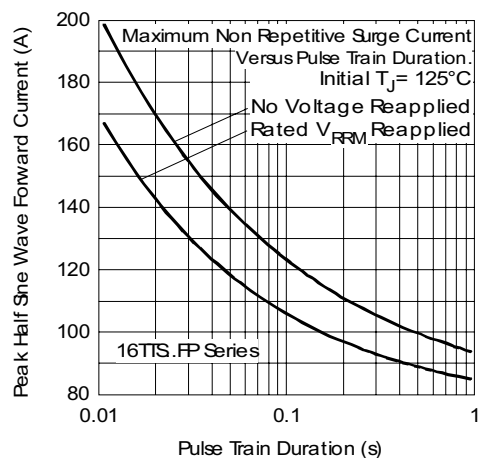


Fig. 6 - Maximum Non-Repetitive Surge Current



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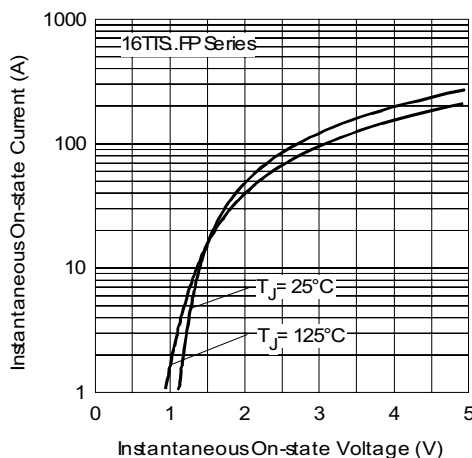


Fig. 7 - On-State Voltage Drop Characteristics

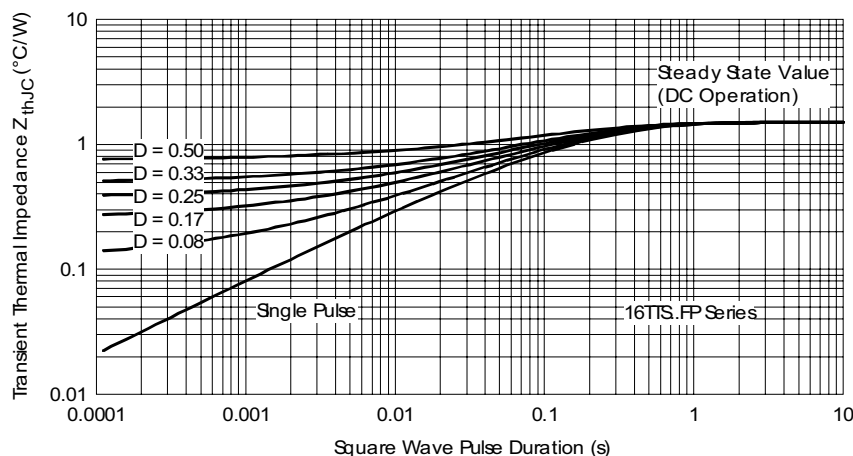


Fig. 8 - Thermal impedance Z_{thJC} Characteristics

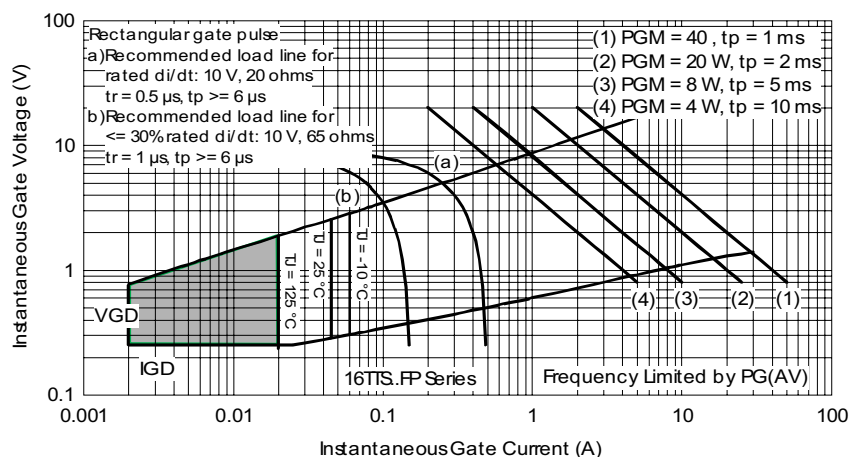


Fig. 9 - Gate Characteristics

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ORDERING INFORMATION TABLE

Device code	16	T	T	S	12	FP	-
	①	②	③	④	⑤	⑥	⑦
①	-	Current rating, RMS value					
②	-	Circuit configuration:					
		T = Single thyristor					
③	-	Package:					
		T = TO-220AB					
④	-	Type of silicon:					
		S = Converter grade					
⑤	-	Voltage code x 100 = V_{RRM}					
		08 = 800 V 12 = 1200 V					
⑥	-	FULL-PAK					
⑦	-	• None = Standard production • PbF = Lead (Pb)-free					

Note: For higher voltage up to 1600 V contact factory

LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95072
Part marking information	http://www.vishay.com/doc?95069



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Vishay

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